TOSHIBA PHOTOCOUPLER GaA&As IRED & PHOTO IC

T L P 5 5 9

DIGITAL LOGIC GROUND ISOLATION

LINE RECEIVER

MICROPROCESSOR SYSTEM INTERFACES

SWITCHING POWER SUPPLY FEEDBACK CONTROL

TRANSISTOR INVERTOR

The TOSHIBA TLP559 consists of a GaAtAs high-output light emitting diode and a high speed detector of one chip photo diodetransistor. This unit is 8-lead DIP package.

TLP559 has no internal base connection, and a Faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

So this is suitable for application in noisy environmental condition.

- Isolation Voltage : 2500Vrms (Min.)
- Switching Speed : $t_{pHL} = 0.3 \mu s$ (Typ.) $t_{pLH} = 0.5 \mu s$ (Typ.) ($R_L = 1.9 k \Omega$)
- TTL Compatible
- **UL** Recognized : UL1577, File No. E67349

PIN CONFIGURATION (TOP VIEW)



SCHEMATIC



961001EBC2

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MAXIMUM RATINGS (Ta = 25° C)

	CHARACTERISTIC			RATING	UNIT	
LED	Forward Current	(Note 1)	IF	25	mA	
	Pulse Forward Current	(Note 2)	I_{FP}	50	mA	
	Peak Transient Forward Current	I _{FPT}	1	Α		
	Reverse Voltage	VR	5	V		
	Diode Power Dissipation	(Note 4)	PD	45	mW	
DETECTOR	Output Current		IO	8	mA	
	Peak Output Current	IOP	16	mA		
	Output Voltage		VO	-0.5~15	V	
	Supply Voltage	V _{CC}	$-0.5 \sim 15$	V		
	Output Power Dissipation	(Note 5)	PO	100	mW	
ng	rating Tomnorotura Rango	т	_55~100	°C.		

Isolation Voltage (AC, 1min., R.H. \leq 60%)	BVs	2500
(Note 7)	DVS	2000

- (Note 1) Derate 0.8mA above 70°C.
- (Note 2) 50% duty cycle, 1ms pulse width. Derate 1.6mA/°C above 70°C.
- (Note 3) Pulse width $\leq 1 \mu s$, 300pps.
- (Note 4) Derate 0.9mW/°C above 70°C.
- (Note 5) Derate 2mW/°C above 70°C.
- (Note 6) Soldering portion of lead : up to 2mm from body of the devise.
- (Note 7) Device considered a two-terminal device : Pins 1, 2, 3, and 4 shorted together and pins 5, 6, 7, and 8 shorted together.

Vrms

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$v_{\mathbf{F}}$	I _F =16mA	_	1.65	1.85	v
	Forward Voltage Temperature Coefficient	$\Delta V_{\mathbf{F}} / \Delta T_{\mathbf{a}}$	$I_F = 16 mA$	_	-2	_	mV/°C
	Reverse Current	IR	$V_R = 5V$			10	μA
	Capacitance Between Terminal	C_{T}	$V_{F}=0, f=1MHz$	_	45	_	pF
ETECTOR	High Level Output Current	I _{OH (1)}	$I_{F}=0mA, V_{CC}=V_{O}=5.5V$	_	3	500	nA
		I _{OH} (2)	$I_{F} = 0 mA, V_{CC} = V_{O} = 15 V$			5	
		IOH	$I_{F}=0mA, V_{CC}=15V$ $V_{O}=15V, Ta=70^{\circ}C$	_	_	50	$\mu \mathbf{A}$
DI	High Level Supply Voltage	ICCH	$I_F=0mA, V_{CC}=15V$	_	0.01	1	$\mu \mathbf{A}$
D	Current Transfer Ratio	I_O / I_F	$I_{F} = 16 \text{mA}, V_{CC} = 4.5 \text{V}$ $V_{O} = 0.4 \text{V}$	20	40	_	%
COUPLED	Low Level Output Voltage	VOL	$I_{F} = 16 \text{mA}, V_{CC} = 4.5 \text{V}$ $I_{O} = 2.4 \text{mA}$	_	l	0.4	v
	Resistance (Input-Output)	RS	R.H. $\leq 60\%$, V _S =500V _{DC} (Note 7)	5×10^{10}	1014	_	Ω
	Capacitance (Input-Output)	CS	$V_S=0, f=1MHz$ (Note 7)		0.8	—	pF

SWITCHING CHARACTERISTICS (Ta = 25° C, V_{CC} = 5V)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Propagation Delay Time $(H \rightarrow L)$	$t_{ m pHL}$	1	I _F =16mA, R _L =1.9k Ω	_	0.2	0.8	$\mu {f s}$
Propagation Delay Time $(L \rightarrow H)$	^t pLH	L		_	0.3	0.8	$\mu {f s}$
Common Mode Transient Immunity at Logic High Output (Note 8)	СМ _Н	2	I _F =0mA, V _{CM} =400Vp-p R _L =4.1k Ω	2000	10000		V/µs
Common Mode Transient Immunity at Logic High Output (Note 8)	CM_{L}	-	IF=16mA, V _{CM} =400Vp-p R _L =4.1k Ω	-2000	-10000		V/µs

(Note 8) CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O < 0.8V$). CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O < 2.0V$). (Note 9) Maximum electrostatic discharge voltage for any ping : 100V (C = 200 pF R =

(Note 9) Maximum electrostatic discharge voltage for any pins : 100V (C=200pF, R=0)

TEST CIRCUIT 1 : Switching Time Test Circuit











